MESD3324PCR

Ultra Low Capacitance Array for ESD Protection

rce mos

The MESD3324PCR provides a typical line to line capacitance of 0.08pF between I/O pins and low insertion loss up to 3GHz providing greater signal integrity making it ideally suited for HDMI applications, such as Digital TVs, DVD players, Computing, set-top boxes and MDDI applications in mobile computing devices.

It has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by ESD(electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients).

Features

- Protects two or four I/O lines
- Low capacitance:0.08pf Typical between I/O channel
- Working voltages : 3.3V
- Low leakage current
- Response Time is < 1 ns
- Meets MSL 1 Requirements
- SCR technology
- ROHS compliant

Main applications

- High Definition Multi-Media Interface (HDMI1.3/1.4/2.0)
- Digital Visual Interface (DVI)
- Display Port Interface
- Serial ATA
- PCI Express
- USB 1.1/2.0/3.0/3.1/OTG
- IEEE 1394 Firewire Ports
- Projection TV Monitors and Flat Panel Displays
- Notebook Computers
- Set Top Box
- Projection TV

Protection solution to meet

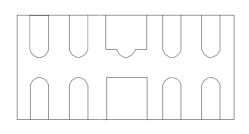
- IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)

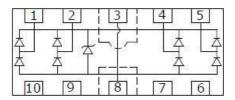
Ordering Information

Device	Marking	Qty per Reel	Reel Size
MESD3324PCR	3324P	3000	7 Inch



DFN2510









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MESD3324PCR

Maximum ratings (Tamb=25°C Unless Otherwise Specified)			
Parameter	Symbol	Value	Unit
ESD Rating per IEC61000-4-2: Contact		18	K V
Air		18	KV
Lead Soldering Temperature	TL	260 (10 sec.)	°C
Operating Temperature Range	τT	-55 ~ 150	°C
Storage Temperature Range	Tstg	-55 ~ 150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

*Other voltages may be available upon request.

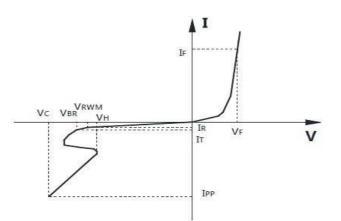
1. Non-repetitive current pulse, per Figure 1.

Electrica	Electrical characteristics (Tamb=25°C Unless Otherwise Specified)					
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
\mathbf{V}_{RWM}	Reverse Working Voltage	Any I/O to Ground			3.3	V
$V_{\scriptscriptstyle BR}$	Reverse Breakdown Voltage	$I_{\rm T} = 0.1 {\rm mA},$	4.0			V
IR	Reverse Leakage Current	$V_{RWM} = 3.3V,$			1	μΑ
V _F	Diode Forward Voltage	$I_F = 15 mA$		0.85	1.2	V
V _h	Hold Current Voltage	$I_H = 10 mA$		1.85		V
N/	V _c Clamping Voltage	$I_{PP} = 1A^{(1)},$			5.7	V
Vс		$I_{PP} = 12A^{(1)},$			11	V
D	dynamia registance	positive transient(TLP)		0.26		Ω
R _{dyn}	dynamic resistance	negative transient(TLP)		0.28		52
C _J ⁽²⁾	C _J ⁽²⁾ Junction Capacitance	$V_{IN} = 2.5V, f = 1MHz,$		0.08	0.13	pF
		between I/O pins				
		V_{IN} = 2.5V, f = 1MHz,		0.35	0.45	рF
		any I/O pin to Ground		0.55	0.45	pF

Notes:(1)Measurements performed using a 100ns Transmission Line Pulse(TLP) system.

(2) Junction capacitance is measured in $V_R=0V$, F=1MHz

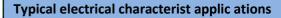
Symbol	Parameter	
V_{RWM}	Working Peak Reverse Voltage	
$V_{\scriptscriptstyle BR}$	Breakdown Voltage @ IT	
Vc	Clamping Voltage @ IPP 100ns	
V C	Transmission Line Pulse(TLP)	
I _T	Test Current	
$I_{\rm RM}$	Leakage current at VRWM	
$I_{\rm PP}$	Peak pulse current	
Co	Off-state Capacitance	
CJ	Junction Capacitance	

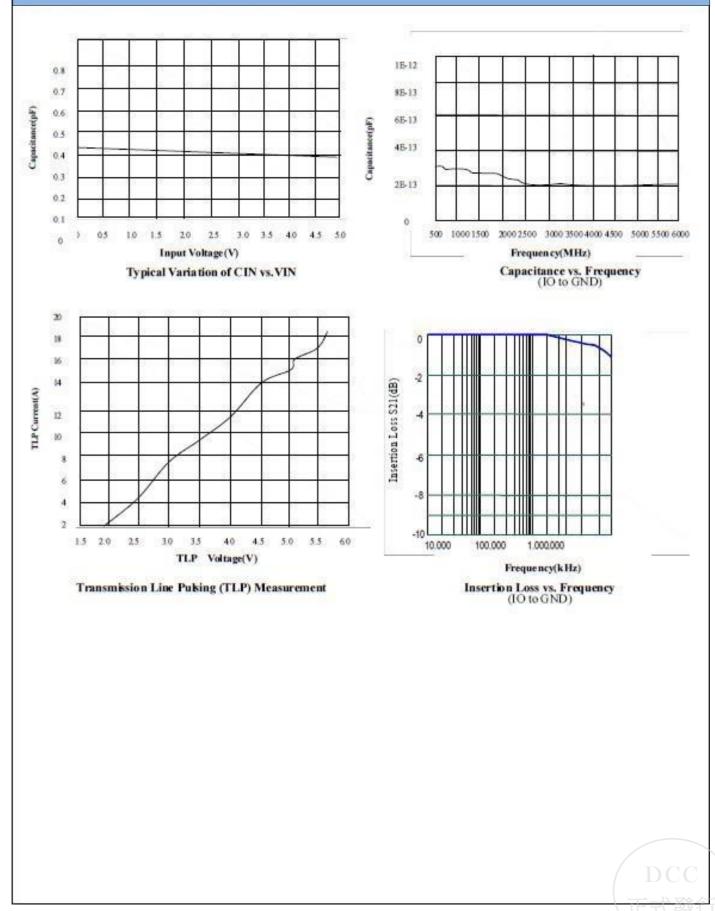




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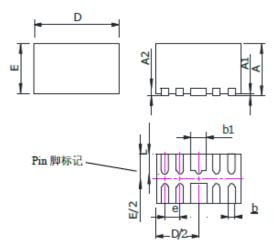
Package Information

DFN2510

Mechanical Data

Case:DFN2510

Case Material: Molded Plastic. ULFlammability



DIM	Millimeters		
	Min	Max	
Α	0.45	0.65	
A1	0.05REF		
A2	0.15REF		
b	0.15	0.25	
b1	0.3	0.5	
D	2.424	2.576	
Ε	0.924 1.076		
e	0.50REF		
L	0.3	0.45	

Recommended Pad outline

